

### SN65LVDS100, SN65LVDT100 SN65LVDS101, SN65LVDT101

SLLS516C-AUGUST 2002-REVISED JUNE 2004

#### DIFFERENTIAL TRANSLATOR/REPEATER

#### **FEATURES**

- Designed for Signaling Rates (1) ≥ 2 Gbps
- Total Jitter < 65 ps</li>
- Low-Power Alternative for the MC100EP16
- Low 100 ps (Max) Part-To-Part Skew
- 25 mV of Receiver Input Threshold Hysteresis Over 0-V to 4-V Common-Mode Range
- Inputs Electrically Compatible With LVPECL, CML, and LVDS Signal Levels
- 3.3-V Supply Operation
- LVDT Integrates 110-Ω Terminating Resistor
- Offered in SOIC and MSOP

#### **APPLICATIONS**

- 622 MHz Central Office Clock Distribution
- High-Speed Network Routing
- Wireless Basestations
- Low Jitter Clock Repeater
- Serdes LVPECL Output to FPGA LVDS Input Translator
- (1) The signaling rate of a line is the number of voltage transitions that are made per second expressed in the units bps (bits per second).

#### **DESCRIPTION**

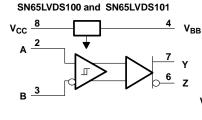
The SN65LVDS100, SN65LVDT100, SN65LVDS101, and SN65LVDT101 are a high-speed differential receiver and driver connected as a repeater. The receiver accepts low-voltage differential signaling (LVDS), positive-emitter-coupled logic (PECL), or current-mode logic (CML) input signals at rates up to 2 Gbps and repeats it as either an LVDS or PECL output signal. The signal path through the device is differential for low radiated emissions and minimal added jitter.

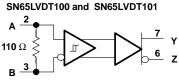
The outputs of the SN65LVDS100 and SN65LVDT100 are LVDS levels as defined by TIA/EIA-644-A. The outputs of the SN65LVDS101 and SN65LVDT101 are compatible with 3.3-V PECL levels. Both drive differential transmission lines with nominally  $100-\Omega$  characteristic impedance.

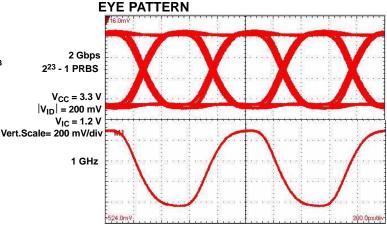
The SN65LVDT100 and SN65LVDT101 include a 110- $\Omega$  differential line termination resistor for less board space, fewer components, and the shortest stub length possible. They do not include the V<sub>BB</sub> voltage reference found in the SN65LVDS100 and SN65LVDS101. V<sub>BB</sub> provides a voltage reference of typically 1.35 V below V<sub>CC</sub> for use in receiving single-ended input signals and is particularly useful with single-ended 3.3-V PECL inputs. When not used, V<sub>BB</sub> should be unconnected or open.

All devices are characterized for operation from –40°C to 85°C.

#### **FUNCTIONAL DIAGRAM**







Horizontal Scale= 200 ps/div



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### **ORDERING INFORMATION**

OUTPUT	TERMINATION RESISTOR	$V_{BB}$	V <sub>BB</sub> PART NUMBER <sup>(1)</sup>		PACKAGE
LVDS	No	Yes	SN65LVDS100D	DL100	SOIC
LVDS	No	Yes	SN65LVDS100DGK	AZK	MSOP
LVDS	Yes	No	SN65LVDT100D	DE100	SOIC
LVDS	Yes	No	SN65LVDT100DGK	AZL	MSOP
LVPECL	No	Yes	SN65LVDS101D	DL101	SOIC
LVPECL	No	Yes	SN65LVDS101DGK	AZM	MSOP
LVPECL	Yes	No	SN65LVDT101D	DE101	SOIC
LVPECL	Yes	No	SN65LVDT101DGK	BAF	MSOP

<sup>(1)</sup> Add the suffix R for taped and reeled carrier (i.e. SN65LVDS100DR).

#### ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range unless otherwise noted

				UNIT		
V <sub>CC</sub>	Supply	voltage range <sup>(2)</sup>		-0.5 V to 4 V		
I <sub>BB</sub>	V <sub>BB</sub> Out	put current		±0.5 mA		
V <sub>I</sub> V <sub>O</sub>	Voltage	range, (A, B, Y, Z)	0 V to 4.3 V			
V <sub>ID</sub>	Differen	tial voltage,  V <sub>A</sub> - V <sub>B</sub>   ('LVDT100	and 'LVDT101 only)	1 V		
		Human Dady Madal(3)	A, B, Y, Z, and GND	±5 kV		
	ESD	Human Body Model (3)	All pins	±2 kV		
		Charged-Device Model (4)	All pins	±1500 V		
P <sub>D</sub>	Continuous power dissipation See Dissipation Ra					

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### **POWER DISSIPATION RATINGS**

PACKAGE	T <sub>A</sub> ≤ 25°C POWER RATING	DERATING FACTOR (1) ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 85°C POWER RATING
DGK	377 mW	3.8 mW/°C	151 mW
D	481 mW	4.8 mW/°C	192 mW

<sup>(1)</sup> This is the inverse of the junction-to-ambient thermal resistance with no air flow installed on the JESD51-3 low effective thermal conductivity test board for leadless surface mount packages.

<sup>(2)</sup> All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

<sup>(3)</sup> Tested in accordance with JEDEC Standard 22, Test Method A114-A.7.

<sup>(4)</sup> Tested in accordance with JEDEC Standard 22, Test Method C101.



#### **RECOMMENDED OPERATING CONDITIONS**

			MIN	NOM	MAX	UNIT
Supply voltage, V <sub>CC</sub>				3.3	3.6	V
Magnitude of differential input valtage IV	'LVDS100 or 'LVDS101		0.1		1	V
Magnitude of differential input voltage  V <sub>ID</sub>	'LVDT100 or 'LVDT101		0.1		0.8	V
Input voltage (any combination of common-mod	e or input signals), V <sub>I</sub>		0		4	V
V <sub>BB</sub> output current, I <sub>O(VBB)</sub>					12	μΑ
Operating free-air temperature, T <sub>A</sub>					85	ů

<sup>(1)</sup> The algebraic convention, in which the less positive (more negative) limit is designated minimum, is used in this data sheet.

#### **ELECTRICAL CHARACTERISTICS**

over recommended operating conditions (unless otherwise specified)

	PARAMETER	TEST CONDITIONS	MIN	TYP (1)	MAX	UNIT
	Supply current, 'LVDx100	No load or input		25	30	^
I <sub>CC</sub>	Supply current, 'LVDx101	$R_L = 50 \Omega$ to 1 V, No input		50	61	mA
	Device power dissipation, 'LVDx100	$R_L = 100 \Omega$ , No input			110	
$P_D$	Device power dissipation, 'LVDx101	Y and Z to $V_{CC}$ - 2 V through 50 $\Omega$ , No input		116	142	mW
$V_{BB}$	Reference voltage output, 'LVDS100 or 'LVDS101	I <sub>O</sub> = -400 μA or 12 μA	V <sub>CC</sub> -1.4	V <sub>CC</sub> -1.35	V <sub>CC</sub> -1.3	mV
SN65LV	DS100 and SN65LVDS101 INPUT CHARACTE	RISTICS (see Figure 1)	!			ļ.
V <sub>IT+</sub>	Positive-going differential input voltage threshold	Occ Figure 4 and Table 4			100	
V <sub>IT-</sub>	Negative-going differential input voltage threshold	See Figure 1 and Table 1	-100			mV
l <sub>i</sub>	Input current	V <sub>I</sub> = 0 V or 2.4 V, Second input at 1.2 V	-20	-	20	μA
•	·	V <sub>I</sub> = 4 V, Second input at 1.2 V			33	μΑ
I <sub>I(OFF)</sub> Power off input current	D	$V_{CC} = 1.5 \text{ V}, V_I = 0 \text{ V or } 2.4 \text{ V},$ Second input at 1.2 V	-20		20	
	Power off input current	$V_{CC}$ = 1.5 V, $V_I$ = 4 V, Second input at 1.2 V			33	μA
I <sub>IO</sub>	Input offset current ( I <sub>IA</sub> - I <sub>IB</sub>  )	$V_{IA} = V_{IB}$ , $0 \le V_{IA} \le 4 \text{ V}$	-6		6	μA
C <sub>i</sub>	Small-signall input capacitance to GND	V <sub>I</sub> = 1.2 V		0.6		pF
SN65LV	DT100 and SN65LVDT101 INPUT CHARACTE	RISTICS (see Figure 1)				
V <sub>IT+</sub>	Positive-going differential input voltage threshold	Occ Figure 4 and Table 4			100	
V <sub>IT-</sub>	Negative-going differential input voltage threshold	See Figure 1 and Table 1	-100			mV
	Landana	V <sub>I</sub> = 0 V or 2.4 V, Other input open	-40		40	
l <sub>l</sub>	Input current	V <sub>I</sub> = 4 V, Other input open			66	μA
	D	V <sub>CC</sub> = 1.5 V, V <sub>I</sub> = 0 V or 2.4 V, Other input open	-40		40	
I <sub>I(OFF)</sub>	Power off input current	$V_{CC}$ = 1.5 V, $V_{I}$ = 4 V, Other input open			66	μA
D	Differential input resistance	$V_{ID}$ = 300 mV or 500 mV, $V_{IC}$ = 0 V or 2.4 V	90	110	132	0
$R_{(T)}$	Differential input resistance	$V_{CC}$ = 0 V, $V_{ID}$ = 300 mV or 500 mV, $V_{IC}$ = 0 V or 2.4 V	90	110	132	Ω
C <sub>i</sub>	Small-signall differential input capacitance	V <sub>I</sub> = 1.2 V		0.6		pF

<sup>(1)</sup> Typical values are with a 3.3-V supply voltage and room temperature



over recommended operating conditions (unless otherwise specified)

	PARAMETER	TEST CONDITIONS	MIN	TYP (1)	MAX	UNIT
SN65LVD	S100 and SN65LVDT100 OUTPUT CHARACTE	RISTICS (see Figure 1)				
V <sub>OD</sub>	Differential output voltage magnitude		247	340	454	
$\Delta  V_{OD} $	Change in differential output voltage magnitude between logic states	See Figure 2	-50		50	mV
V <sub>OC(SS)</sub>	Steady-state common-mode output voltage		1.125		1.375	٧
$\Delta V_{OC(SS)}$	Change in steady-state common-mode output voltage between logic states	See Figure 3	-50		50	mV
V <sub>OC(PP)</sub>	Peak-to-peak common-mode output voltage			50	150	mV
Ios	Short-circuit output current	$V_{O(Y)}$ or $V_{O(Z)} = 0$ V	-24		24	mA
I <sub>OS(D)</sub>	Differential short-circuit output current	V <sub>OD</sub> = 0 V	-12		12	mA
SN65LVD	S101 and SN65LVDT101 OUTPUT CHARACTE	RISTICS (see Figure 1)				
.,	High level output valtage	50 $\Omega$ to V <sub>CC</sub> – 2 V, See Figure 4	V <sub>CC</sub> -1.25	V <sub>CC</sub> -1.02	V <sub>CC</sub> -0.9	V
V <sub>OH</sub>	High-level output voltage	V <sub>CC</sub> = 3.3 V, 50-Ω load to 2.3 V	2055	2280	2405	mV
		50 $\Omega$ to V <sub>CC</sub> - 2 V, See Figure 4	V <sub>CC</sub> -1.83	V <sub>CC</sub> -1.61	V <sub>CC</sub> -1.53	V
V <sub>OL</sub>	Low-level output voltage	V <sub>CC</sub> = 3.3 V, 50-Ω load to 2.3 V	1475	1690	1775	mV
V <sub>OD</sub>	Differential output voltage magnitude	50- $\Omega$ load to V <sub>CC</sub> – 2 V, SeeFigure 4	475	575	750	mV

#### **SWITCHING CHARACTERISTICS**

over recommended operating conditions (unless otherwise noted)

PARAMETER			TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
	Propagation delay time, 'LVDx100			300	470	800	20
t <sub>PLH</sub>	low-to-high-level output	'LVDx101		400	630	900	ps
	Propagation delay time,	'LVDx100		300	470	800	20
t <sub>PHL</sub>	high-to-low-level output	'LVDx100	See Figure 5	400	630	900	ps
t <sub>r</sub>	Differential output signal rise time (2	0%–80%)				220	ps
t <sub>f</sub> Differential output signal fall time (20%–80%)					220	ps	
t <sub>sk(p)</sub>	Pulse skew ( t <sub>PHL</sub> - t <sub>PLH</sub>  ) (2)				5	50	ps
t <sub>sk(pp)</sub>	Part-to-part skew <sup>(3)</sup>		V <sub>ID</sub> = 0.2 V, See Figure 5			100	ps
t <sub>jit(per)</sub>	RMS period jitter (4)		1 GHz 50% duty cycle square wave input,		1	3.7	ps
t <sub>jit(cc)</sub>			$V_{ID} = 200 \text{ mV}, V_{IC} = 1.2 \text{ V}, \text{ See Figure 6}$		6	23	ps
t <sub>jit(pp)</sub>	t <sub>jit(pp)</sub> Peak-to-peak jitter		2 GHz PRBS, $2^{23}$ –1 run length, $V_{ID}$ = 200 mV, $V_{IC}$ = 1.2 V, See Figure 6		28	65	ps
t <sub>jit(det)</sub> Peak-to-peak deterministic jitter <sup>(6)</sup>		2 GHz PRBS, $2^7$ –1 run length, $V_{ID}$ = 200 mV, $V_{IC}$ = 1.2 V, See Figure 6		17	48	ps	

<sup>(1)</sup> All typical values are at 25°C and with a 3.3 V supply.

 $t_{sk(p)}$  is the magnitude of the time difference between the  $t_{PLH}$  and  $t_{PHL}$  of any output of a single device.  $t_{sk(pp)}$  is the magnitude of the time difference in propagation delay time between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

Period jitter is the deviation in cycle time of a signal with respect to the ideal period over a random sample of 1000,000 cycles.

Cycle-to-cycle jitter is the variation in cycle time of a signal between adjacent cycles, over a random sample of 1,000 adjacent cycle

Deterministic jitter is the sum of pattern-dependent jitter and pulse-width distortion.



#### PARAMETER MEASUREMENT INFORMATION

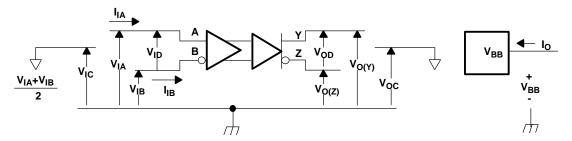


Figure 1. Voltage and Current Definitions

**Table 1. Receiver Input Voltage Threshold Test** 

APPLIED	VOLTAGES	RESULTING DIFFERENTIAL INPUT VOLTAGE	RESULTING COMMON- MODE INPUT VOLTAGE	OUTPUT <sup>(1)</sup>
VIA	V <sub>IB</sub>	V <sub>ID</sub>	V <sub>IC</sub>	
1.25 V	1.15 V	100 mV	1.2 V	Н
1.15 V	1.25 V	−100 mV	1.2 V	L
4.0 V	3.9 V	100 mV	3.95 V	Н
3.9 V	4. 0 V	–100 mV	3.95 V	L
0.1 V	0.0 V	100 mV	0.05 V	Н
0.0 V	0.1 V	−100 mV	0.05 V	L
1.7 V	0.7 V	1000 mV	1.2 V	Н
0.7 V	1.7 V	-1000 mV	1.2 V	L
4.0 V	3.0 V	1000 mV	3.5 V	Н
3.0 V	4.0 V	-1000 mV	3.5 V	L
1.0 V	0.0 V	1000 mV 0.5 V		Н
0.0 V	1.0 V	-1000 mV	0.5 V	L

(1) H = high level, L = low level

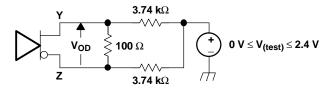
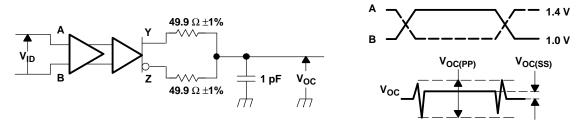


Figure 2. SN65LVDx100 Differential Output Voltage (VoD) Test Circuit



NOTE: All input pulses are supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 0.25$  ns, pulse repetition rate (PRR) = 0.5 Mpps, pulse width =  $500 \pm 10$  ns .  $C_L$  includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T. The measurement of  $V_{OC(PP)}$  is made on test equipment with a -3 dB bandwidth of at least 300 MHz.

Figure 3. Test Circuit and Definitions for the SN65LVDx100 Driver Common-Mode Output Voltage



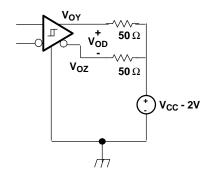
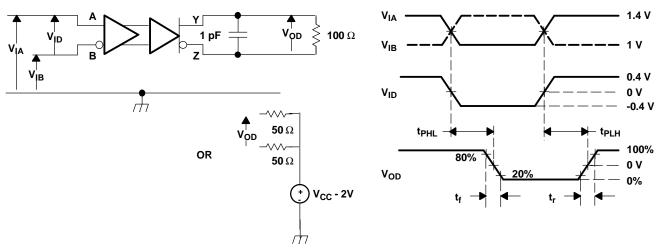


Figure 4. Typical Termination for LVPECL Output Driver (65LVDx101)



NOTE: All input pulses are supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 0.25$  ns, pulse repetition rate (PRR) = 50 Mpps, pulse width =  $10 \pm 0.2$  ns.  $C_L$  includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T. Measurement equipment provides a bandwidth of 5 GHz minimum.

Figure 5. Timing Test Circuit and Waveforms

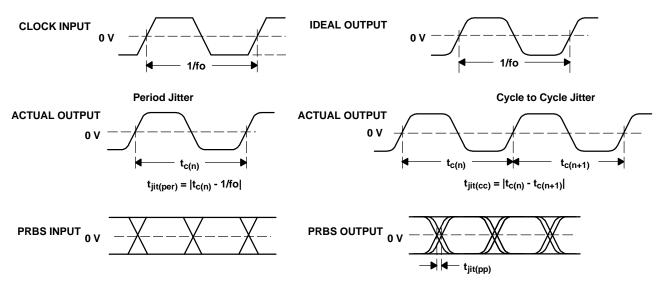
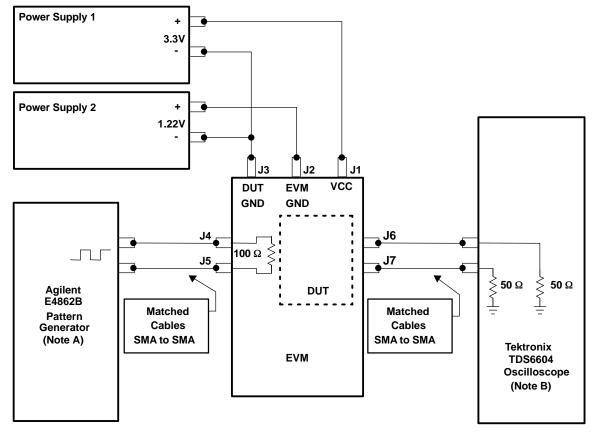


Figure 6. Driver Jitter Measurement Waveforms

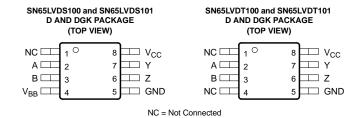




- A. Source jitter is subtracted from the measured values.
- B. TDS JIT3 jitter analysis software installed

Figure 7. Jitter Setup Connections for SN65LVDS100 and SN65LVDS101

#### **PIN ASSIGNMENTS**



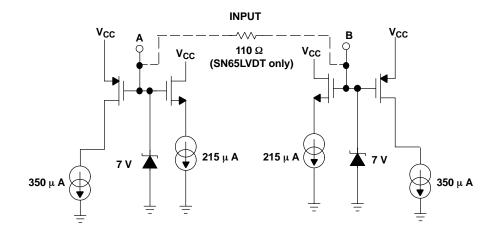
#### **FUNCTION TABLE**

DIFFERENTIAL INPUT	OUTPU	TS <sup>(1)</sup>
$V_{ID} = V_A - V_B$	Υ	Z
V <sub>ID</sub> ≥ 100 mV	Н	L
-100 mV < V <sub>ID</sub> < 100 mV	?	?
V <sub>ID</sub> ≤ − 100 mV	L	Н
Open	?	?

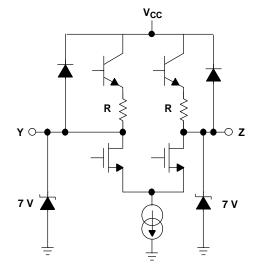
(1) H = high level, L = low level, ? = indeterminate



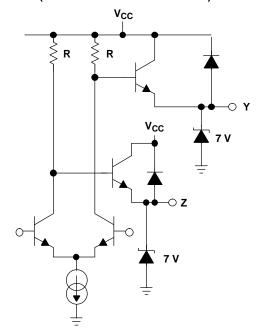
#### **EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS**



OUTPUT (SN65LVDS100 and SN65LVDT100)



OUTPUT (SN65LVDS101 and SN65LVDT101)





#### TYPICAL CHARACTERISTICS

**SUPPLY CURRENT** 

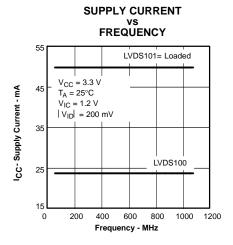


Figure 8.

**SN65LVDS100** 

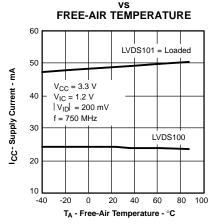


Figure 9.

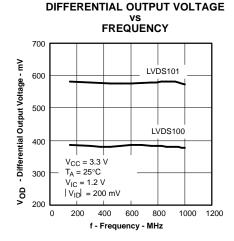
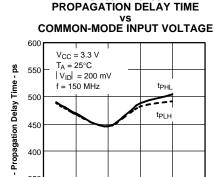


Figure 10.



р

300

 $V_{IC}$  - Common-Mode Input Voltage - V Figure 11.

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# SN65LVDS101 PROPAGATION DELAY TIME VS COMMON-MODE INPUT VOLTAGE 750 V<sub>CC</sub> = 3.3 V T<sub>A</sub> = 25°C

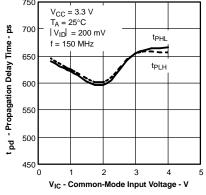


Figure 12.

# SN65LVDS100 PROPAGATION DELAY TIME VS FREE-AIR TEMPERATURE 550 V<sub>CC</sub> = 3.3 V |V<sub>ID</sub>| = 200 mV |f = 150 MHz

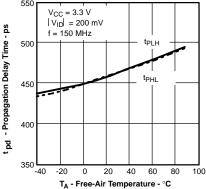


Figure 13.

# SN65LVDS101 PROPAGATION DELAY TIME VS FREE-AIR TEMPERATURE

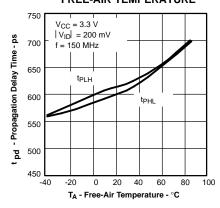


Figure 14.

#### SN65LVDS100 PEAK-TO-PEAK JITTER VS FREQUENCY

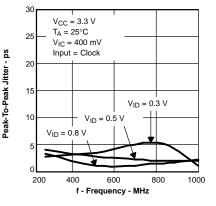


Figure 15.

#### SN65LVDS100 PEAK-TO-PEAK JITTER VS DATA RATE

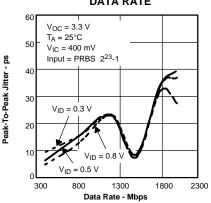
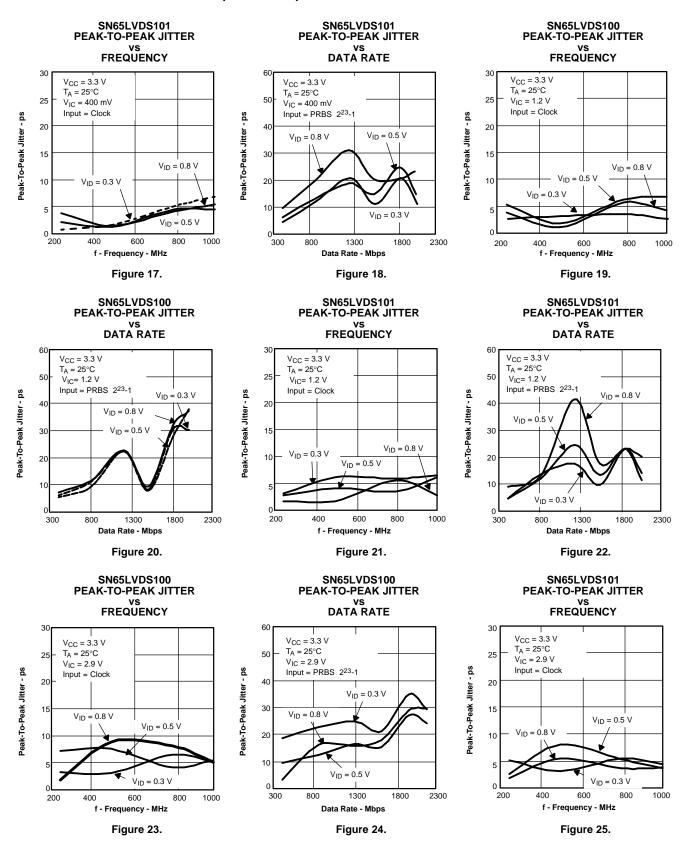
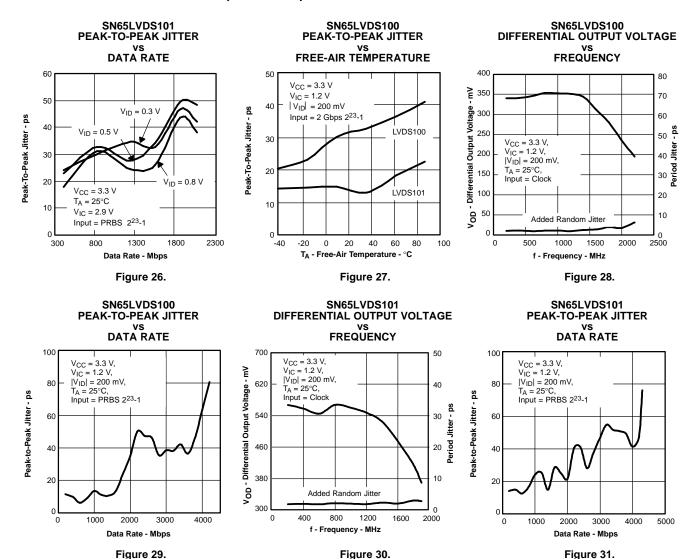


Figure 16.



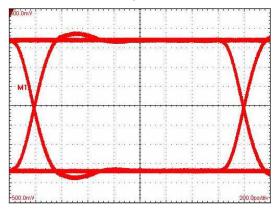












Horizontal Scale= 200 ps/div LVPECL-to-LVDS

Figure 32.

SN65LVDS101 622 Mbps, 2<sup>23</sup>– 1 PRBS

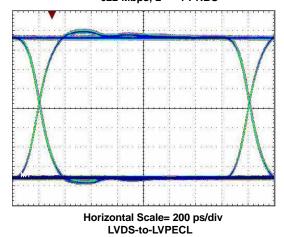
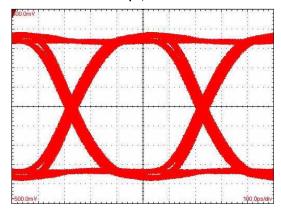


Figure 34.

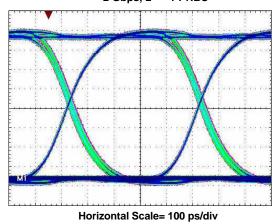
SN65LVDS100 2 Gbps, 2<sup>23</sup>– 1 PRBS



Horizontal Scale= 100 ps/div LVPECL-to-LVDS

Figure 33.

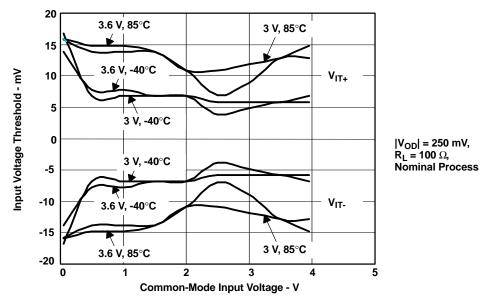
SN65LVDS101 2 Gbps, 2<sup>23</sup>– 1 PRBS



LVDS-to-LVPECL

Figure 35.





NOTE: V<sub>IT</sub> is a steady-state parameter. The switching time is influenced by the input overdrive above this steady-state threshold up to a differential input voltage magnitude of 100 mV.

Figure 36. SN65LVDS100 Simulated Input Voltage Threshold vs Common-Mode Input Voltage, Supply Voltage, and Temperature



#### **APPLICATION INFORMATION**

The SN65LVDS100, SN65LVDT100, SN65LVDS101, and SN65LVDT101 inputs will detect a 100-mV difference between any two signals between 0 V and 4 V, This range will allow receipt of many different single-ended and differential signals. Following are some of the more common connections.

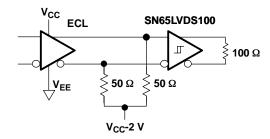


Figure 37. PECL-to-LVDS Translation

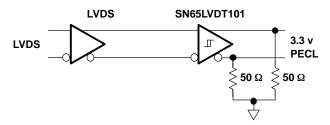


Figure 38. LVDS-to-3.3 V PECL Translation

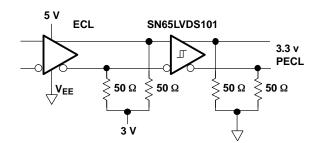


Figure 39. 5-V PECL to 3.3-V PECL Translation

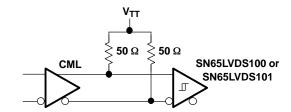


Figure 40. CML-to-LVDS or 3.3-V PECL Translation



#### **APPLICATION INFORMATION (continued)**

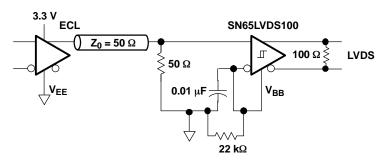


Figure 41. Single-Ended 3.3-V PECL-to-LVDS Translation

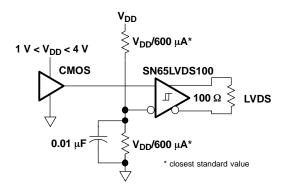


Figure 42. Single-Ended CMOS-to-LVDS Translation

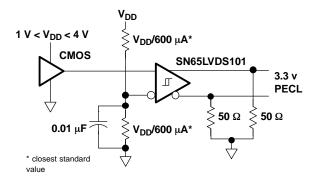


Figure 43. Single-Ended CMOS-to-3.3-V PECL Translation

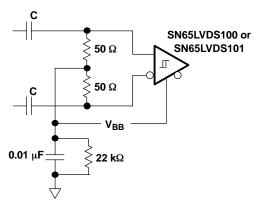


Figure 44. Receipt of AC-Coupled Signals



#### **APPLICATION INFORMATION (continued)**

#### **FAILSAFE CONSIDERATIONS**

Failsafe, in regard to a line receiver, usually means that the output goes to a defined logical state with no input signal. To keep added jitter to an absolute minimum, the SN65LVDS100 does not include this feature. It does exhibit 25 mV of input voltage hysteresis to prevent oscillation and keep the output in the last state prior to input-signal loss (assuming the differential noise in the system is less than the hysteresis).

Should failsafe be required, it may be added externally with a 1.6-k $\Omega$  pull-up resistor to the 3.3-V supply and a 1.6-k $\Omega$  pull-down resistor to ground as shown in Figure 45 The default output state is determined by which line is pulled up or down and is the user's choice. The location of the 1.6-k $\Omega$  resistors is not critical. However the 100- $\Omega$  resistor should be located at the end of the transmission line.

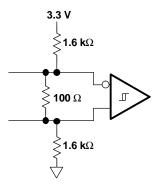


Figure 45. External Failsafe Circuit

Addition of this external failsafe will reduce the differential noise margin and add jitter to the output signal. The roughly 100-mV steady-state voltage generated across the  $100-\Omega$  resistor adds (or subtracts) from the signal generated by the upstream line driver. If the line driver's differential output is symmetrical about zero volts, then the input at the receiver will appear asymmetrical with the external failsafe. Perhaps more important, is the extra time it takes for the input signal to overcome the added failsafe offset voltage.

In Figure 46 and using an external failsafe, the high-level differential voltage at the input of the SN65LVDS100 reaches 340 mV and the low-level –400 mV indicating a 60-mV differential offset induced by the external failsafe circuitry. The figure also reveals that the lowest peak-to-peak time jitter does not occur at zero-volt differential (the nominal input threshold of the receiver) but at –60 mV, the failsafe offset.

The added jitter from external failsafe increases as the signal transition times are slowed by cable effects. When a ten-meter CAT-5 UTP cable is introduced between the driver and receiver, the zero-crossing peak-to-peak jitter at the receiver output adds 250 ps when the external failsafe is added with this specific test set up. If external failsafe is used in conjunction with the SN65LVDS100, the noise margin and jitter effects should be budgeted.



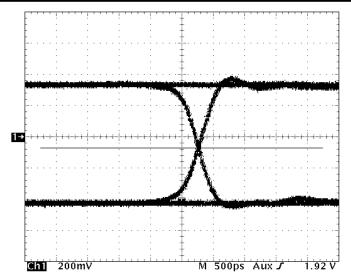


Figure 46. Receiver Input Eye Pattern With External Failsafe





#### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
SN65LVDS100D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS100DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS100DGK	ACTIVE	MSOP	DGK	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS100DGKG4	ACTIVE	MSOP	DGK	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS100DGKR	ACTIVE	MSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS100DGKRG4	ACTIVE	MSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS100DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS100DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS101D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS101DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS101DGK	ACTIVE	MSOP	DGK	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS101DGKG4	ACTIVE	MSOP	DGK	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS101DGKR	ACTIVE	MSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS101DGKRG4	ACTIVE	MSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS101DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS101DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT100D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT100DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT100DGK	ACTIVE	MSOP	DGK	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT100DGKG4	ACTIVE	MSOP	DGK	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT100DGKR	ACTIVE	MSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT100DGKRG4	ACTIVE	MSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT100DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT100DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT101D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM



#### PACKAGE OPTION ADDENDUM

5-Oct-2007

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
SN65LVDT101DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT101DGK	ACTIVE	MSOP	DGK	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT101DGKG4	ACTIVE	MSOP	DGK	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT101DGKR	ACTIVE	MSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT101DGKRG4	ACTIVE	MSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT101DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDT101DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

<sup>&</sup>lt;sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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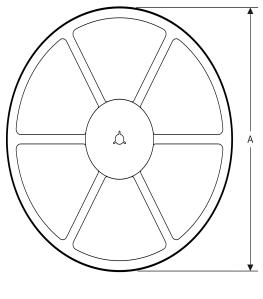
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### PACKAGE MATERIALS INFORMATION

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#### TAPE AND REEL INFORMATION

#### **REEL DIMENSIONS**





#### **TAPE DIMENSIONS**



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### TAPE AND REEL INFORMATION

\*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65LVDS100DGKR	MSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
SN65LVDS100DGKR	MSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
SN65LVDS100DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65LVDS101DGKR	MSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
SN65LVDS101DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65LVDT100DGKR	MSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
SN65LVDT100DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
SN65LVDT101DGKR	MSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
SN65LVDT101DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

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\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LVDS100DGKR	MSOP	DGK	8	2500	338.1	340.5	21.1
SN65LVDS100DGKR	MSOP	DGK	8	2500	358.0	335.0	35.0
SN65LVDS100DR	SOIC	D	8	2500	367.0	367.0	35.0
SN65LVDS101DGKR	MSOP	DGK	8	2500	358.0	335.0	35.0
SN65LVDS101DR	SOIC	D	8	2500	367.0	367.0	35.0
SN65LVDT100DGKR	MSOP	DGK	8	2500	358.0	335.0	35.0
SN65LVDT100DR	SOIC	D	8	2500	367.0	367.0	35.0
SN65LVDT101DGKR	MSOP	DGK	8	2500	358.0	335.0	35.0
SN65LVDT101DR	SOIC	D	8	2500	367.0	367.0	35.0

# DGK (S-PDSO-G8)

# PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- E. Falls within JEDEC MO-187 variation AA, except interlead flash.



## D (R-PDSO-G8)

#### PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



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